

MS2209

RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

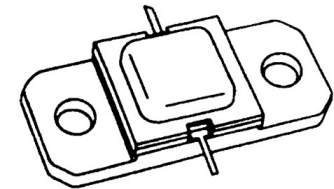
Features

- 225 MHz BANDWIDTH
- COMMON BASE
- GOLD METALLIZATION
- CLASS C OPERATION
- POUT = 90 W MIN. WITH 13 dB GAIN

DESCRIPTION:

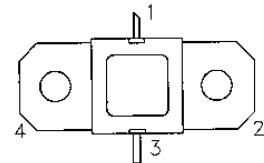
The MS2209 is a broadband, high peak pulse power silicon NPN bipolar device specifically designed for avionics applications requiring broad bandwidth with moderate duty cycles and pulse width constraints such as ground/ship based DME/TACAN.

This device is also designed for specialized applications including JTIDS applications when duty cycle is moderately higher. Gold metallization and emitter ballasting assure high reliability under Class C amplifier operation.



.400 x .400 2NLFL (M218)
hermetically sealed

PIN CONNECTION



1. Collector 3. Emitter
2. Base 4. Base

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
V _{CC}	Collector Supply Voltage	50	V
I _C	Device Current	7.0	A
P _{DISS}	Power Dissipation	220	W
T _J	Junction Temperature (RF Pulsed Operation)	+200	°C
T _{STG}	Storage Temperature	-65 to +200	°C

Thermal Data

R _{TH(J-C)}	Junction-case Thermal Resistance	0.80	°C/W
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ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV _{CBO}	I _C = 40mA	I _E = 0mA	65	---	---	V
BV _{EBO}	I _E = 10mA	I _C = 0mA	3.0	---	---	V
BV _{CER}	I _C = 40mA	R _{BE} = 10Ω	65	---	---	V
I _{CBO}	V _{CB} = 50 V		-----	---	12	mA
h _{FE}	V _{CE} = 5 V	I _C = 2A	20	---	120	---

DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P _{OUT}	f = 960-1215MHz	V _{CC} = 50V	P _{IN} = 13W	90	100	---	W
G _P	f = 960-1215MHz	V _{CC} = 50V	P _{IN} = 13W	8.4	---	---	dB
η _C	f = 960-1215MHz	V _{CC} = 50V	P _{IN} = 13W	38	44	---	%

Pulse Width = 10 μs
Duty Cycle = 10%

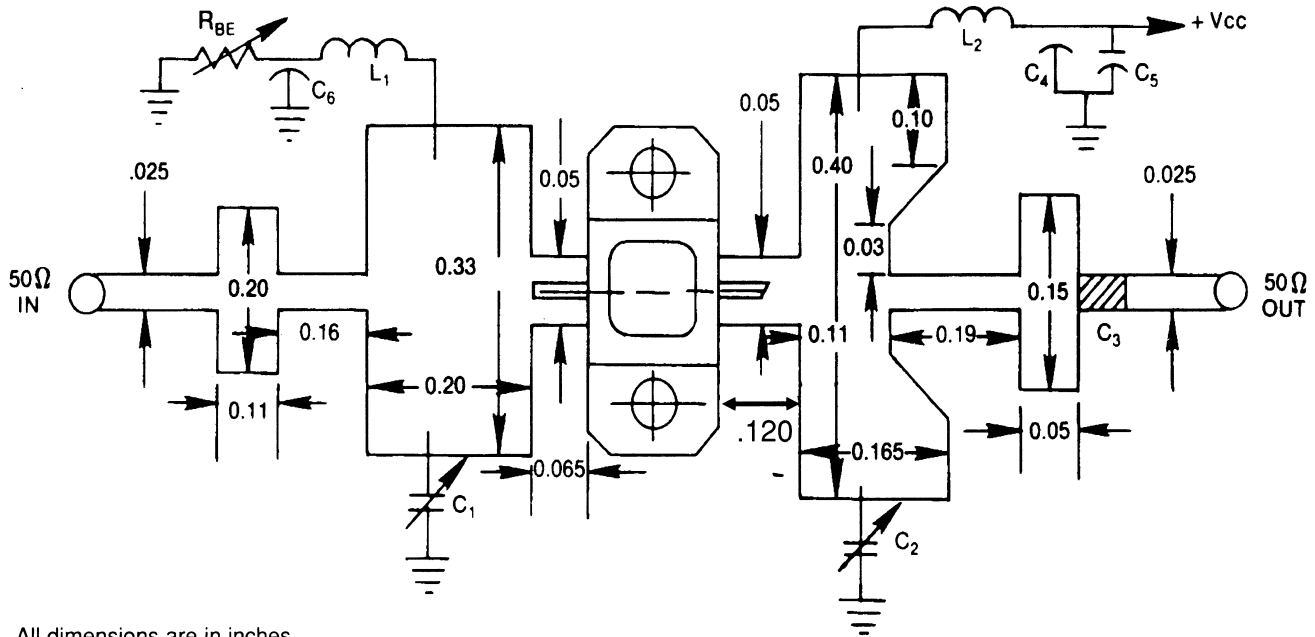
IMPEDANCE DATA

Freq	Z _{in} (Ω)	Z _{cl} (Ω)
960	5+j9.0	10.2-j8.8
1025	6+j8.0	9.5-j7.6
1090	6.8+j7.2	9.0-j6.2
1150	6.3+j7.0	8.4-j5.0
1215	5.8+j7.8	7.0-j3.7

V_{cc}=50v
P_{out}=90w

TEST CIRCUIT

Ref. Dwg. No. J-313120



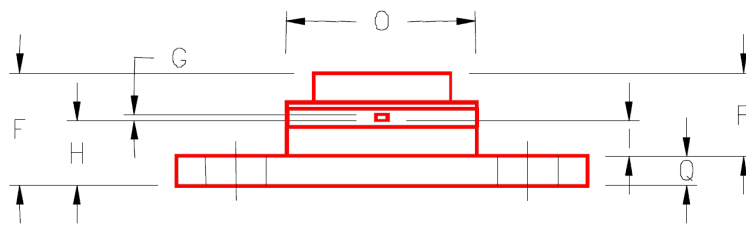
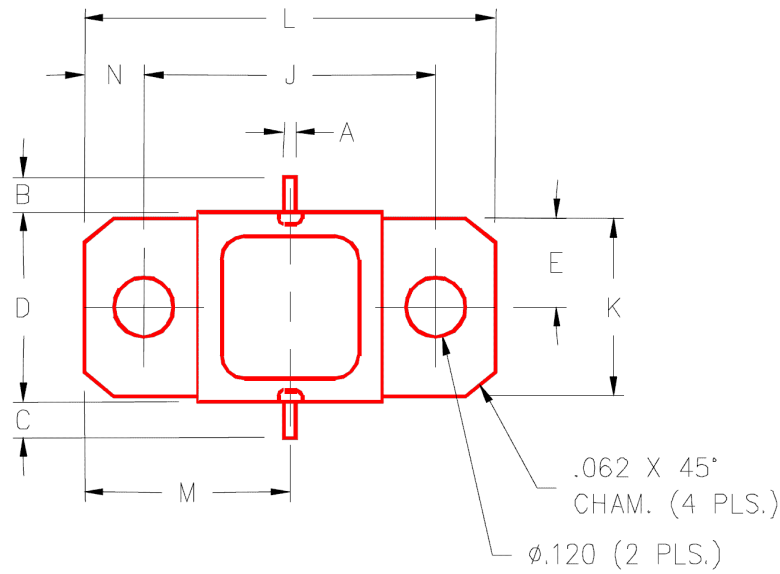
All dimensions are in inches.
Substrate material: .025 thick Al₂O₃

C1,C2: 0.3 - 3.5 pF Johanson Capacitors, or Equiv.
C3 : 100 pF Chip Capacitor
C4,C6: 1500 pF RF Feedthru

C5 : 100 MF, Electrolytic 50V
L1,L2 : No. 32 Wire, 4 Turn .062 I.D.
RBE : 0 - 1.0 Ohm

PACKAGE MECHANICAL DATA

PACKAGE STYLE M218



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.025/0,64		J	.650/16,51	
B	.100/2,54		K	.386/9,80	
C	.100/2,54		L	.900/22,86	
D	.395/10,03	.407/10,34	M	.450/11,43	
E	.193/4,90		N	.125/3,18	
F		.230/5,84	O	.405/10,29	
G	.004/0,10	.007/0,18	P		.170/4,32
H	.118/3,00	.131/3,33	Q	.062/1,58	
I	.063/1,60				